Contents

Abstract (in Chinese)……………………………………………………………………I
Abstract (in English)…………………………………………………….................III
Acknowledgement……………………………………………………………………V
Contents……………………………………………………………………………...VI
Table Lists………………………………………………………………………....VIII
Figure Captions……………………………………………………………………..IX

Chapter 1 Introduction
1.1 General Background and Motivation………...………………………….…………1
1.2 Introduction to Poly-3-hexylthiophene,P3HT…..…………………………..…………1
1.3 OTFTs beased on P3HT with Bottom-Contact Structure……………………………...3
1.4 Operation of Organic Thin Film Transistor…………………………………………3
1.5 Thesis Organization………………………………………………………………...4

Chapter 2 Low Temperature Process of P3HT OTFTs with LPD SiO_2 as Insulator
2.1 Introduction…………………………………………………………………………...12
2.2 Chemical Vapor Deposition(CVD) and Liquid-Phase Depotition(LPD)………..…..12
2.3 Mechanism of LPD……………………………………………………………….…..14
2.4 Experimental Detail
2.4.1 Process flow of OTFTs based on P3HT with SiO_2 as gate insulator by PECVD and LPD…………………………………………………………………..….15
2.4.2 Process flow of OTFTs based on P3HT with SiO_2 as gate insulator and isolation layer by LPD…………………………………………………………………16
2.5 Electrical Characteristics of OTFTs based on P3HT
2.5.1 Measurement…………………………………………………………..…….17
2.5.2 Threshold Voltage and OFF Current Definition……………………………..18
2.5.3 The Extraction Method of Mobility……………...………………………………18
2.6 Results and Discussion
2.6.1 Characteristics of LPD SiO_2………………...…………………………….……19
2.6.2 Characteristics of OTFTs with LPD SiO_2 as gate insulator……………………19
2.6.3 Characteristics of OTFTs with LPD SiO_2 as gate insulator and isolationlayer.20
2.7 Summry…………………………………………………………………………….22

Chapter 3 Plasma Treatment Effects on OTFTs
3.1 Introduction…………………………………………………………………………40
3.2 Experimental Detail……………………………………………………...…………41

3.3 Results and Discussion……………………………………………………………….42

Chapter 4 Conclusion and future work
4.1 Conclusions
4.1.1 Low Temperature Process of OTFTs with LPD SiO_2 as Gate Insulator………60
4.1.2 Plasma Treatment Effects on OTFTs…………………………………………….61
4.2 Future work
4.2.1 A new method to deposit P3HT thin film………………………………………61
4.2.2 Thermal stability of P3HT OTFTs……………………………………………..62
4.2.3 An in-situ pacivation layer for protecting the P3HT film………………………62
4.2.4 New gate insulator materials for P3HT OTFTs…………………………………62

Reference……………………………………………………………………………….63
Vita……………………………………………………………………………………...67

Table Lists

Chapter 1

Table 1-1 Characteristics of some of the most commonly used organic semiconductors

Chapter 2

Table2-1 The magnitude of I_{OFF} with different channel length and different channel width

Table 2-2 Field-effect Mobility, Off state leakage and I_{ON}/I_{OFF} of OTFTs with PECVD SiO_2, LPD SiO_2 and LPD SiO_2 with isolation dielectric layer.

Chapter 3

Table 3-1 Summary of field-effect mobility and threshold voltage with respect to O_2 plasma exposure time.

Table 3-2 Summary of field-effect mobility and threshold voltage with respect to N_2O plasma exposure time.

Table 3-3 Summary of field-effect mobility and threshold voltage with respect to NH_3 plasma exposure time.

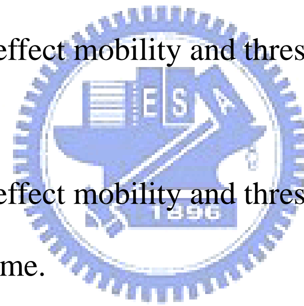

Figure Captios

Chapter 1

Figure 1-1 Molecular structure of poly-3-hexylthiophene

Figure 1-2 Two different orientations of ordered P3HT lamella structure with respect to the substrate

Figure 1-3 OTFT device configurations：(a)Top-contact device, with source and drain electrodes evaporated onto the organic semiconducting layer through a mask. (b) Bottom-contact device, with the organic semiconductor deposited onto the gate insulator and the prefabricated source and drain electrodes[1.13].

Figure 1-4 (a)the schematic diagram of bottom-contact OTFT. (b)the layout of comb structure for source and drain electrodes

Figure 1-5 Schematic of operation modes of organic thin film transistor, showing a lightly p-doped semiconductor： + indicates a positive charge in semiconductor ; - indicate a negative charge counterion(a) no-bais (b) accumulation mode (c) depletion mode (d) channel pinch-off.

Chapter 2

Figure 2-1 The schematic diagram of the apparatus for LPD

Figure 2-2 Process flow of OTFTs based on P3HT with SiO_2 as gate insulator by PECVD and LPD

Figure 2-3 Process flow of OTFTs based on P3HT with SiO_2 as gate insulator and isolation layer by LPD.

Figure 2-4 High frequency of C-V curve of LPD SiO_2

Figure 2-5 I-V curve of MOS capacitors with LPD SiO_2

Figure 2-6 Gate leakage current of OTFTs based on P3HT with LPD SiO_2 amd PECVD SiO_2

Figure 2-7 Gate leakage path of OTFTs at (a)positive gate bias (b) negative gate bias.

Figure 2-8 The transfer characteristics I_S-V_G of OTFTs with LPD SiO2 and PECVD SiO2 as gate insulator

Figure 2-9 The gate leakage current of OTFTs with and without LPD SiO2 as isolation layer

Figure 2-10 The output characteristics I_S-V_G of OTFTs with and without LPD SiO_2 as isolation layer

Figure 2-11 (a) The output characteristics I_S-V_D of OTFTs without isolation layer (b)current path of OTFTs without isolation layer

Figure 2-12 (a) The output characteristics I_S-V_D of OTFTs with LPD SiO_2 as isolation layer (b)current path of OTFTs with isolation layer

Chapter 3

Figure 3-1 Process flow of OTFTs with plasma treatment on SiO_2 prior to the deposition of P3HT.

Figure 3-2 The output characteristcs I_S-V_G of OTFTs with O_2 plasma treatment prior to the deposition of P3HT.

Figure 3-3 Variation of field-effect mobility with respect to O_2 plasma exposure time.

Figure 3-4 Variation of threshold voltage with respect to O_2 plasma exposure time.

Figure 3-5 The output characteristics I_S-V_D of OTFTs with O_2 plasma treatment prior to the deposition of P3HT.

Figure 3-6 The output characteristcs I_S-V_G of OTFTs with N_2O plasma treatment prior to the deposition of P3HT

Figure 3-7 Variation of field-effect mobility with respect to N_2O plasma exposure time.

Figure 3-8 Variation ofthreshold voltage with respect to N_2O plasma exposure time.

Figure 3-9 The output characteristics I_S-V_D of OTFTs with N_2O plasma treatment prior to

the deposition of P3HT

Figure 3-10 The output characteristcs I_S-V_G of OTFTs with NH_3 plasma treatment prior to the deposition of P3HT

Figure 3-11 Variation of field-effect mobility with respect to NH_3 plasma exposure time

Figure 3-12 Variation of threshold voltage with respect to NH_3 plasma exposure time

Figure 3-13 The output characteristics I_S-V_D of OTFTs with NH_3 plasma treatment prior to the deposition of P3HT